

ASSIGNMENT - 1

1) List out the semiconductor products and its corresponding companies.

Ans	Company	Product
i)	TSMC (Taiwan Semiconductor manufacturing company)	service for manufacturing semiconductors
ii)	NVIDIA Corporation	GPU's, Processors, AI and Deep Learning hardware
iii)	Advanced Micro Devices (AMD)	CPU, GPU's, SOC
iv)	Intel Corporation	microprocessor, SSD, FPGA, Graphics software
v)	Qualcomm Incorporated	Mobile processor, GPU's, Modem,
vi)	Samsung Electronics	Memory (DRAM, Flash) Processors, Image Sensors
vii)	Texas Instruments	Analog IC, DSP, microcontroller

2) What are the latest laptop processors from AMD, Intel and Apple: Frequency and node

Ans

i) Intel

i9-14900K or i9 14th gen

Clock speed :- upto 6.0 GHz

Process node :- 10 nm or Intel 7

ii) AMD

Ryzen 9 7950X3D

clock speed :- upto 5.7 GHz

Process node :- 5 nm

iii) Apple

M3 Max

Clock speed :- upto 4.05 GHz

Process node :- 3 nm

3) What are the latest mobile processors available from Qualcomm and mediatek : Frequency and node

Ans Qualcomm :

Snapdragon Gen 3

clock speed :- 3.3 GHz

Process node :- 4 nm

Mediatek :-

Dimensity 9300

Clock speed :- 3.25 GHz

Process node :- 4 nm

4) What are the different job roles available in VLSI field.

Ans i) VLSI Design Engineers

ii) Verification Engineers

iii) Physical Design Engineers

iv) ASIC Design Engineers

v) FPGA Design Engineers

vi) Design Automation Engineers

vii) Analog / Mixed Signal design Engineers

viii) CAD Engineers

ix) SOC Architect

x) RF Design Engineers

5) Why there is a shift from BJT - MOSFET - FINFET in detail.

Ans Reasons why there was a shift from BJT to MOSFET:

i) Power Efficiency - MOSFETs consume less power compared to BJTs, because they have a very high input impedance and draw negligible input current when in a static state.

ii) Minature MOSFETs allow for easier minaturization of devices due to their simpler structure and compatibility with IC fabrication processes.

iii) CMOS Technology: CMOS technology, which uses MOSFETs, became popular for its low power consumption, making it a standard choice for digital IC.

Reasons for shift from MOSFET to FinFET.

i) Leakage Current: As transistor sizes decreased, leakage current became significant concern in MOSFETs. FinFETs with their 3D structure help this issue by providing better control over current.

ii) Scaling and Performance: FinFET enables better scaling of transistor dimensions, allowing for the continuation of Moore's law. It provides better performance and energy efficiency.

iii) Subthreshold Slope: FinFETs exhibit better subthreshold slope characteristics, which means they can switch between on and off states more effectively reducing power consumption during switching.

6) Evolution of memory technology

Ans

1) Vacuum Tubes and Delay lines:

- Early computers used vacuum tubes memory storage. There were large, power-hungry, and had limited capacity.
- Delay lines were also used involving delay of acoustic waves through a medium to represent binary data.

2) Magnetic core memory

- Introduced in 1950s, it used small magnetized rings to store bits, providing faster and more reliable data storage.

3) DRAM (Dynamic Random Access Memory)

- Introduced in 1960s, DRAM relies on the charge stored in capacitors to represent bits. It's widely used due to its higher density compared to other.

4) SRAM (Static RAM)

- SRAM, introduced around same time as DRAM uses flip flops to store bits. It is faster than DRAM but costlier and lower density.

5) Flash Memory or NAND memory

- Flash memory, introduced in 1980s, revolutionized non-volatile storage. It is used in USB drives, memory cards and SSDs. Flash memory stores data in floating gate transistors.

6) SDRAM (Synchronous Dynamic RAM)

- SDRAM introduced in 1990s, synchronized memory operations with clock speed of CPU providing faster data rates compared to DRAM.

7) DDR (Double Data Rate) SDRAM

DDR SDRAM, starting with DDR in early 2000s, improved data transfer rates by transferring data on both rising and falling edges of clock.

8) 3D NAND Flash

3D NAND introduced in 2010s stacked memory cells vertically increasing storage density and overcoming some limitations of Flash NAND.